

## Section I. (Amendment to the Claims)

A listing of claims 1-22 of the present application, which are amended herein with markings to show changes made, is provided below:

1. (Currently amended) A method for forming a semiconductor structure comprising the steps of:

providing a structure having at least one wire bond pad in contact with a metal line of an interconnect structure, said at least one wire bond pad having an exposed surface portion;

forming a metallic cap on at least the exposed upper surface portion of the wire bond pad, said metallic cap comprises a TiN seed layer with a Ti or Al layer atop and is resistant to alkaline attack; and

forming Ni/Au metallization on said metallic cap, wherein the Ni/Au metallization comprises a Ni layer overlaid by an Au layer, wherein the Ni layer is formed by electroless deposition of Ni and wherein the Au layer is formed by immersion deposition of Au followed by electroless deposition of Au.

2. (Original) The method of Claim 1 wherein the metallic cap is formed on the exposed surface portion of the wire bond pad through an opening formed in an overlying passivation stack.

3. (Original) The method of Claim 1 wherein the metallic cap is formed atop an entire surface of a metal layer and then the metallic cap and metal layer are selectively etched to form the metallic cap on at least the exposed upper surface portion of the wire bond pad.
4. (Original) The method of Claim 1 wherein the metal line is comprised of Cu.
5. (Original) The method of Claim 1 wherein said structure further includes a barrier and a lower passivation layer formed atop the interconnect structure.
6. (Original) The method of Claim 1 wherein the wire bond pad is comprised of Al or an aluminum alloy.
7. (Cancelled).
8. (Currently amended) The method of Claim 1 wherein the ~~metallic cap comprises TiN/Ti or TiN/Al~~ TiN seed layer of the metallic cap has a thickness of about 500 Å or less, and wherein the Ti or Al layer of the metallic cap has a thickness less than about 10000 Å.
9. (Previously presented) The method of Claim 8 wherein the metallic cap comprises an Al layer that is cleaned/pretreated prior to forming the Ni/Au metallization.
10. (Previously presented) The method of Claim 8 wherein the metallic cap comprises a Ti layer that is activated prior to forming the Ni/Au metallization.

11. (Original) The method of Claim 1 further comprising forming a barrier layer between at least the metal bond pad and the metal line.
12. (Original) The method of Claim 1 wherein said metal bond pad and said metal line are in contact through a via opening formed in a lower passivation layer that is located on said interconnect structure.
- 13-20. (Cancelled).
21. (Previously presented) The method of Claim 1 further comprising bonding a wire to said Ni/Au metallization.
22. (Currently amended) A method for forming a semiconductor structure comprising the steps of:
  - providing a structure having at least one wire bond pad in contact with a metal line of an interconnect structure, said at least one wire bond pad having an exposed surface portion;
  - forming a metallic cap on at least the exposed upper surface portion of the wire bond pad, said metallic cap comprises a TiN seed layer with a Ti or Al layer atop and is resistant to alkaline attack;
  - forming Ni/Au metallization on said metallic cap, wherein said Ni/Au metallization comprises a Ni layer overlaid by an Au layer; and
  - bonding a wire to said Ni/Au metallization.